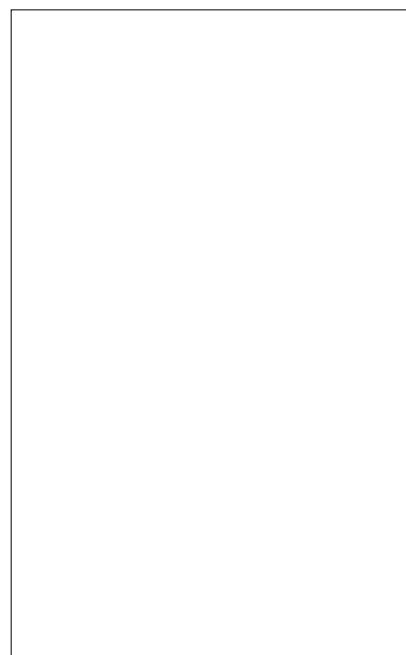


**JCT840CH 40A SCR**

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT840CH SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220C is RoHS compliant.

**MAIN FEATURES****ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
Average on-state current ($T_c=134^\circ\text{C}$)	$I_{T(AV)}$	25	A
RMS on-state current ($T_c=134^\circ\text{C}$)	$I_{T(RMS)}$	40	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	500	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^\circ\text{C}$)		540	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1250	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	10	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	10	A
Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W

ORDERING INFORMATION

J	CT	8	40	C	H
JieJie Microelectronics Co., Ltd.	SCRs	8:V _{DRM} /V _{RRM} 800V	I _{T(RMS)} :40A	C:TO-220C	High junction temperature

MARKING

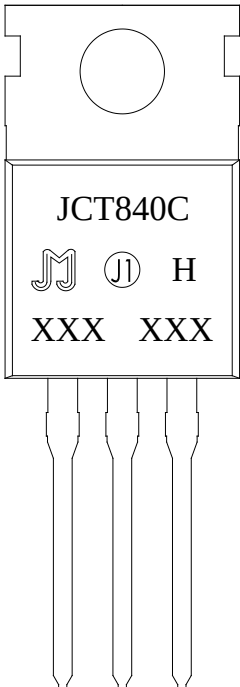
 JCT840C  J1 H XXX XXX	XXX XXX Year _____ Month _____ Production Code
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FIG.1: Maximum power dissipation versus RMS on-state current

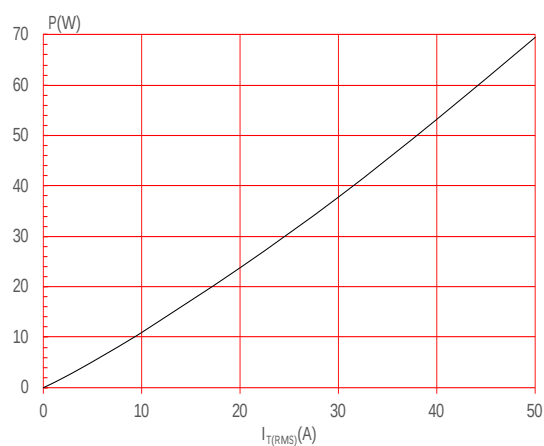


FIG.2: RMS on-state current versus case temperature

